

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										外形	備考		
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルス h _{FE}		バイアス		h _{FE}	h _{ie} #	h _{re} #	h _{oe} #	f _{αb} #			C _{ob}	r _{bb'}
									I _{ce0} (V)	I _c (mA)	V _{CE} (V)	I _e (mA)	h _{FE} *	h _{ie} # (Ω)	h _{re} # (×10 ⁻⁴)	h _{oe} # (μS)	f _{αb} # (Mc)	C _{ob} (pF)	r _{bb'} h _{ie} (real) # (Ω)			
1	2	3	4	5					6		7			8				9	10		11	12

- 1** TYPE NUMBER
- 2** ORIGINAL MANUFACTURER
- 3** USES
- 4** MATERIAL AND STRUCTURE
- 5** MAXIMUM RATINGS
- 6** I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7** STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8** STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- 9** f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T.
 - 10** C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11** OUTLINE
 - 12** REMARKS
- *: とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外形	備考			
				V _{CB0} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値		直流又はパルス h _{FE}		バイアス		h _{FE}	h _{ie} *	h _{ie} *	h _{re} *	h _{oe} *			f _{ab} f _T *	C _{ob}	τ _{bb} h _{ie} (real)*
									(μA)	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)										
2SC1034	ソニー	PA. SW	Si. TMe	1100	13	1A	25W (T _c =25°C)	150	5mA	800	18	3	750	10	-200					5*	95	C _c f _{ab} 220pS	100	
★	1035	三洋	LN	Si. TP	30	3	20	150	150	1	25	100	6	1	6	-3	NF = 6dB (f = 800MHz, 11V, 2mA)		700*	0.7	C _c f _{ab} 2.5pS	205C		
★	1036	"	RF	"	30	3	20	150	150	1	25	100	6	1	6	-3			700*	0.7	C _c f _{ab} 2.5pS	205C		
"	1037	日電	PA	Si. E	60	4	4A	50W (T _c =25°C)	175	1mA	30	50	10	1A									111	
"	1038	"	"	"	40	3	150	3.75W (T _c =25°C)	175	50	20	15~200	10	70	10	-70	P _o = 800mW (f = 2.3GHz, V _{ce} = 18V, P _i = 250mW)		2000*	2.5		129		
"	1039	"	"	"	40	3	250	7.5W (T _c =25°C)	175	100	20	15~200	10	100	10	-100	P _o = 1.4W (f = 2.3GHz, V _{ce} = 18V, P _i = 630mW)		2000*	4		129		
"	1040	"	"	"	45	4	1.2A	15W (T _c =25°C)	175	1mA	30	15~200	10	1A									184	
"	1041	"	"	"	40	3	150	3.75W (T _c =25°C)	175	50	20	15~200	10	70	10	-70	P _o = 900mW (f = 2GHz, V _{ce} = 18V, P _i = 250mW)		2000*	2.5		129		
"	1042	"	"	"	40	3	250	7.5W (T _c =25°C)	175	100	20	15~200	10	100	10	-100	P _o = 1.6W (f = 2GHz, V _{ce} = 18V, P _i = 630mW)		2000*	4		129		
"	1043	"	RF. LN	"	45	3	300	6W (T _c =25°C)	175	0.1	30	80	10	100	15	-50	P _C = 15dB (f = 500MHz, 50mA) NF = 3.5dB (f = 200MHz, 50mA)		2200*	2.5		129		
"	1044	"	RF	"	45	4	30	250	200	50nA	30	100	6	6	6	-6	G _p = 22dB (f = 200MHz)		1000*	NF = 3dB (f = 200MHz)		50C		
★	1045	三洋	RF. PA	Si. T	1000	5	1A	25W (T _c =25°C)	125	5	100	25~200	15	200										
★	1046	"	PA	Si. TMe	1000	6	3A	25W (T _c =25°C)	150	100	100	8	5	2A	5	-100				4*	150	35	102	
"	1047	松下	RF	Si. EP	30	3	15	150	125	10	30	120	6	1	6	-1			650*	C _{re} 0.88pF	30	138		
★	1048	三洋	"	Si. Me	200	6	50	600	150	10	100	90	10	25	10	-10			120*	3.5		84B		
"	1049	"	"	"																				
"	1050	三洋	PA	Si. TMe	300	6	1A	40W (T _c =25°C)	150	1mA	150	90	5	300	5	-300				5*	50		102	
"	1051	"	"	"	150	6	7A	60W (T _c =25°C)	150	1mA	30	90	5	1A	5	-1A				8*	230		102	
★	1052	富士通	SW	Si. EP	75	5	1A	800	175	0.5	50	40	1	500			t _{on} < 50nS, t _{off} < 70nS t _{sig} < 40nS						84B	
★	1053	"	"	"	75	5	700	800	175	0.2	40	50	1	500			t _{on} < 40nS, t _{off} < 60nS t _{sig} < 45nS						84B	
★	1054	"	RF. LN	"	35	3	50	180	175	0.5	12	60	6	1	6	-2	NF = 3dB (f = 200MHz, 6V, 1mA)		700*	1	30*	205C		
"	1055	日立	PA. SW	Si. T	130	6	7A	25W (T _c =25°C)	175	200	30	60	4	5A			t _{on} = 0.4μS, t _{off} = 4μS t _{sig} = 35μS							153
★	1056	ソニー	RF	Si. PaMe	260	5	100	750	175	1	100	150	5	3	20	-20				180*	7		181	
★	1057	富士通	PA	Si. EP	50	3.5	1A	12W (T _c =25°C)	175	500	20	50	5	500			P _o = 6.5W (V _{ce} = 24V, f = 700MHz, P _i = 2W)						133	
★	1058	"	"	"	50	3.5	2A	20W (T _c =25°C)	175	1mA	20	50	5	1A			P _o = 11.5W (V _{ce} = 24V, f = 700MHz, P _i = 4W)						133	
★	1059	日立	"	"	300	4	150	8W (T _c =25°C)	150			60	10	50									153	
"	1060	"	PA	Si. T	50	4	3A	25W (T _c =25°C)	150	100	20	35~320	4	1A	4	-500				8*	100		267	
"	1061	"	"	"	50	4	3A	25W (T _c =25°C)	150	100	20	35~320	4	1A	4	-500				8*	100		268	
"	1062	富士通	SW	Si. TMe	200	4	100	700	175	2	100	60	2	50			t _{on} < 3.2μS, t _{off} < 12μS t _{sig} < 8μS				5		84B	
★	1063	ソニー	"	Si. DB	10	5	1A	750	150	1	10	60	1	65			t _{on} < 60nS, t _{off} < 100nS t _{sig} < 300nS						84C	

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